# 2SB1504

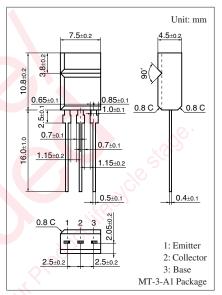
### Silicon PNP epitaxial planar type darlington

#### For power switching

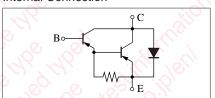
- High forward current transfer ratio hFE
- High-speed switching
- Allowing automatic insertion with radial taping

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V	
Collector current	$I_{C}$	-8	A	
Peak collector current	$I_{CP}$	-12	A	
Collector power dissipation	P <sub>C</sub>	1.5	W	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



#### Internal Connection



### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

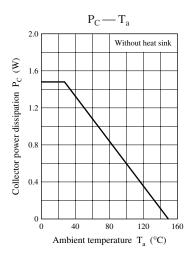
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -30 \text{ mA}, I_B = 0$	-50	250		V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$	-W		-100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -7 \text{ V}, I_C = 0$	7.9		-2	mA
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -3 \text{ V}, I_{C} = -4 \text{ A}$	1 000		10 000	_
	h <sub>FE2</sub>	$V_{CE} = -3 \text{ V}, I_{C} = -8 \text{ A}$	500			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -4 \text{ A}, I_B = -8 \text{ mA}$			-1.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -4 \text{ A}, I_B = -8 \text{ mA}$			-2.0	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 0.5 \text{ A}, f = 200 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = -4 \text{ A}, I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		0.5		μs
Storage time	t <sub>stg</sub>	$V_{CC} = -50 \text{ V}$		2.0		μs
Fall time	t <sub>f</sub>			1.0		μs

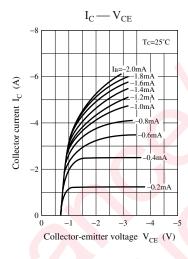
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

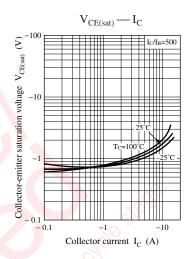
#### 2. \*: Rank classification

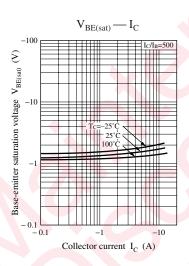
Rank	Р	Q	R
h <sub>FE1</sub>	1000 to 2500	2000 to 5000	4000 to 10000

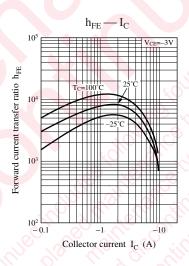
Publication date: April 2003 SJD00080BED 1

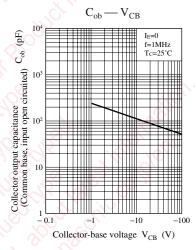


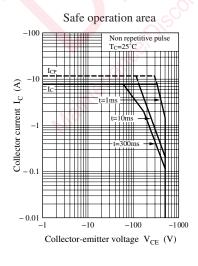


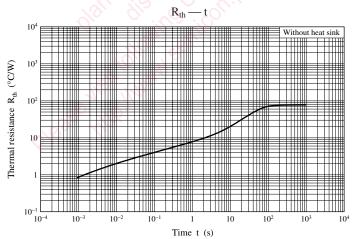












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